WWF Raw Is War SmackDown Complete Year 2000 AVI 7370G

SmackDown - Year-by-Year History (1 of 19). These are the people who wrestle for the belt!1. Field of the Invention The present invention relates to a pattern-forming method, and in particular, to a pattern-forming method for a semiconductor device, which can perform fine patterning without deteriorating an etching selectivity between a silicon substrate and a high-permittivity substrate such as a plasma CVD SiO2 film. 2. Description of the Related Art Recently, the miniaturization of an element and the reduction of a power consumption have been strongly demanded in the manufacturing of semiconductor devices such as the manufacture of LSIs. With regard to the reduction of the power consumption, it has been a big problem to decrease a parasitic capacitance and an equivalent resistance. The parasitic capacitance causes the power consumption to be increased due to a potential variation in a substrate circuit caused by a capacitance between the substrate and a power supply terminal. The equivalent resistance causes the increase in a resistance between the substrate and the power supply terminal. In view of these problems, a capacitor formed in a peripheral portion of an LSI chip to store a power supply has been replaced with a low-capacitance capacitor such as a MIM capacitor, thereby reducing a parasitic capacitance of the substrate. For a lower wiring material, a power supply wiring has been replaced with a thin film such as TiW. However, although a low-capacitance capacitor and a power supply wiring are used, this is not enough to significantly reduce a power consumption. Meanwhile, a technique for using a high-permittivity film (SiO2, for example) of a plasma CVD system in place of a silicon substrate has been developed. For the use of the high-permittivity film, a technique in which a gate electrode is formed using the high-permittivity film has been proposed (for example, in Japanese Patent Laid-Open No. 2002-357945). However, in the gate electrode using the high-permittivity film, the etching rate in the formation of a wiring material is largely decreased in comparison with that in the silicon substrate. Therefore, in order to form a wiring material (metal wiring), an etching mask such as a silicon nitride film should be formed to sufficiently maintain the etching selectivity with respect to the high-permittivity film. However, when the high-permittivity 82157476af